PHPT61006NY

100 V, 6 A NPN high power bipolar transistor

26 January 2015

Product data sheet

1. **General description**

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61006PY

Features and benefits 2.

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

Applications

- Power management
- Load switch
- Linear mode voltage regulator
- **Backlighting applications**
- Motor drive
- Relay replacement

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	12	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; $t_p \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C; pulsed	-	35	57	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В
3	Е	emitter	q <u> </u>	, M
4	В	base		E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	- Sylli123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61006NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61006NY	1006NAB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

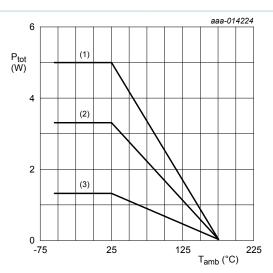
Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	100	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	12	Α
I _B	base current			-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

^[3] Device mounted on an ceramic PCB; Al₂O₃, standard footprint.

^[4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uity a)	thermal resistance from junction to ambient		[1]	-	-	115	K/W
			<u>[2]</u>	-	-	45	K/W
			<u>[3]</u>	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

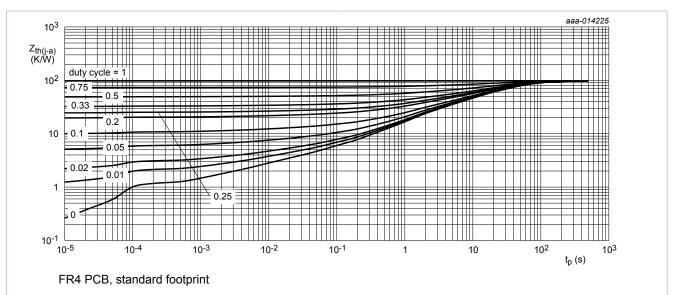


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

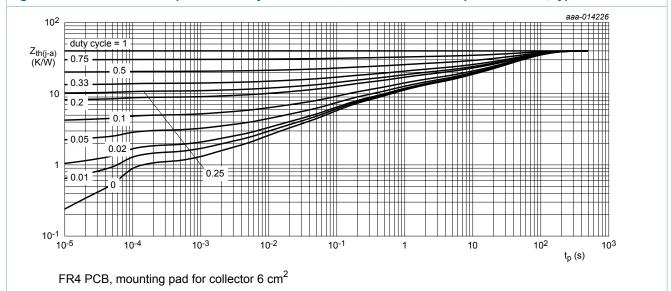


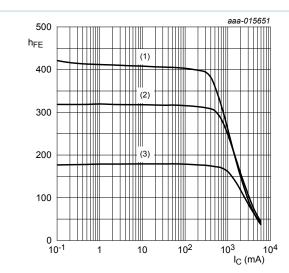
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-СВО	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	140	260	-	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{CE} = 2 \text{ V}; I_{C} = 1 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	120	210	-	
		V_{CE} = 2 V; I_{C} = 3 A; t_{p} ≤ 300 μ s; δ ≤ 0.02; T_{amb} = 25 °C	50	90	-	
		V_{CE} = 2 V; I_{C} = 6 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	25	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	45	65	mV
		$I_C = 3 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	100	150	mV
		I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	210	340	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; $t_p \le 300 \mu s$; $δ \le 0.02$; T_{amb} = 25 °C; pulsed	-	35	57	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	0.85	1	V
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	1.05	1.3	V
		I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	1.1	1.3	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 500 mA; T_{amb} = 25 °C	-	0.7	0.9	V
t _d	delay time	V_{CC} = 12.5 V; I_C = 3 A; I_{Bon} = 150 mA;	-	10	-	ns
t _r	rise time	I _{Boff} = -150 mA; T _{amb} = 25 °C	-	365	-	ns
t _{on}	turn-on time		-	375	-	ns
t _s	storage time		-	285	-	ns
t _f	fall time		-	385	-	ns
t _{off}	turn-off time		-	670	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	-	170	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	22	-	pF



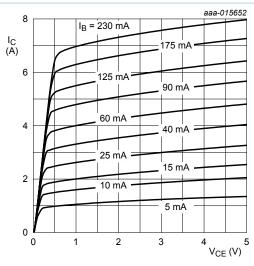
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

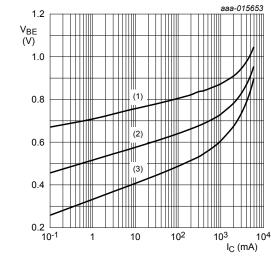
(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



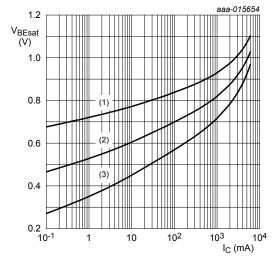
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

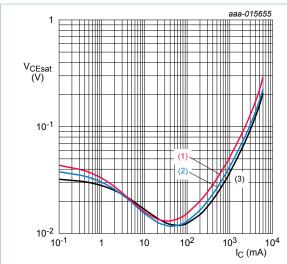
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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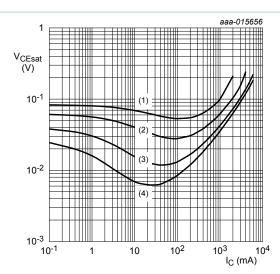
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

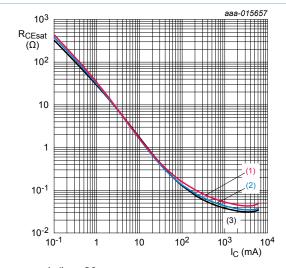
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

(4)
$$I_{\rm C}/I_{\rm B} = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



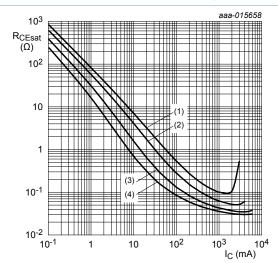
 $I_C/I_B = 20$

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

(1)
$$I_C/I_B = 100$$

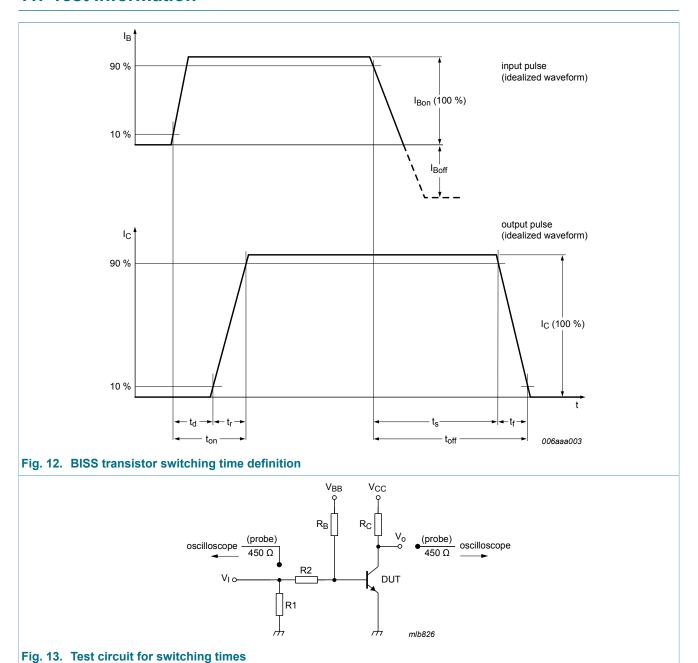
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

(4)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information



11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

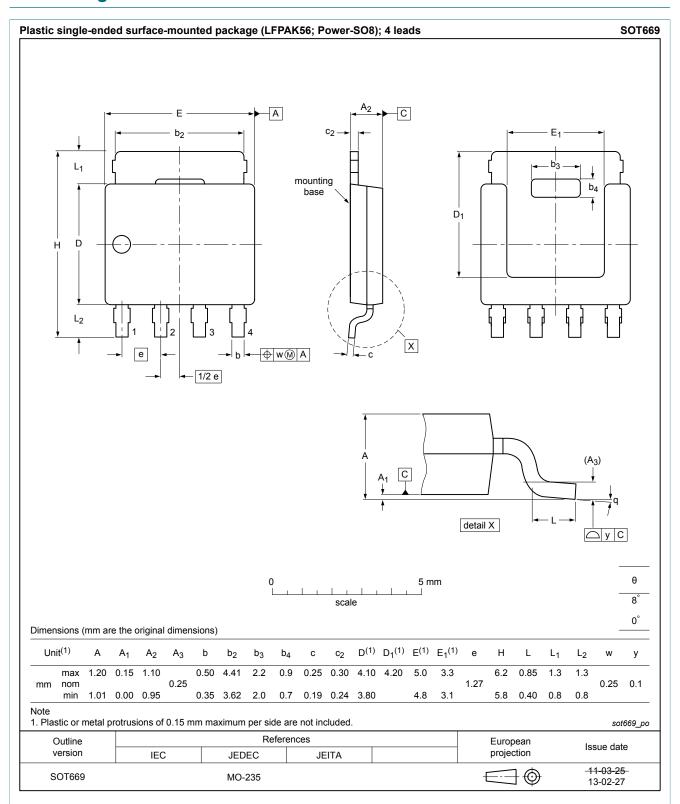


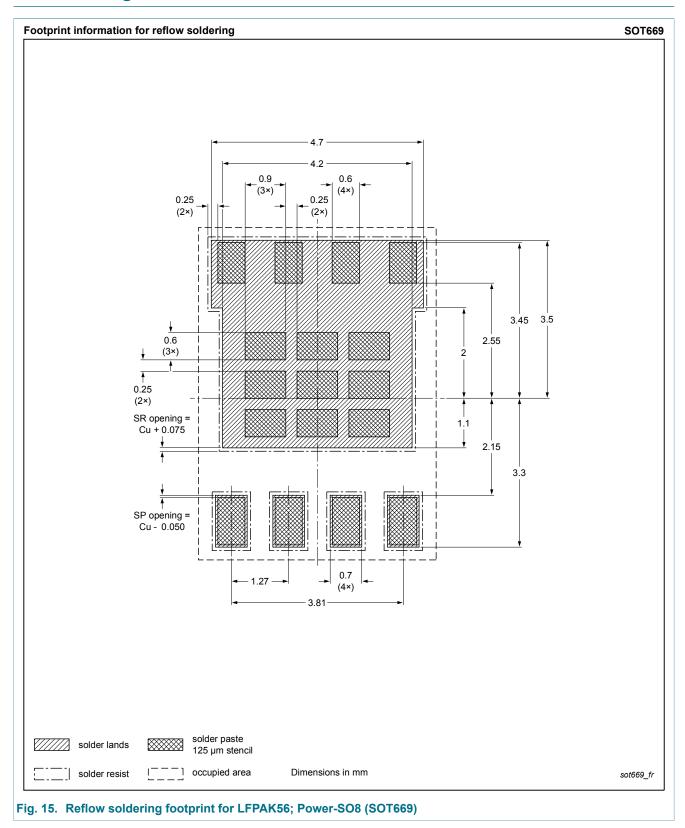
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61006NY v.1	20150126	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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